

1. (Amended) A method of reducing film growth rate when growing a carbon- or boron-doped silicon film or silicon-germanium film, comprising:

Q1
sub B' }
carbon or boron-doping while supplying a silicon precursor and optionally a germanium precursor to a substrate, at reduced pressure of about 0.1 to 100 millitorr, wherein said step of doping while supplying includes supplying a dopant precursor to the substrate according to a relationship of the precursors as shown in Fig. 2.

15. (Amended) A method of growing a film without sharp pressure transitions, comprising:

Q2
sub C1
B2 }
carbon or boron-doping while supplying a silicon precursor and optionally a germanium precursor to a substrate, at reduced pressure of about 0.1 to 100 millitorr, wherein said step of doping while supplying includes supplying a dopant precursor to the substrate according to a relationship of the precursors as shown in Fig. 2.

REMARKS

Applicant amended independent claims 1 and 15 for additional clarity.

Applicant includes a Letter to the Official Draftsman per comment 2.